



JX020V 2A Sensitive SCR

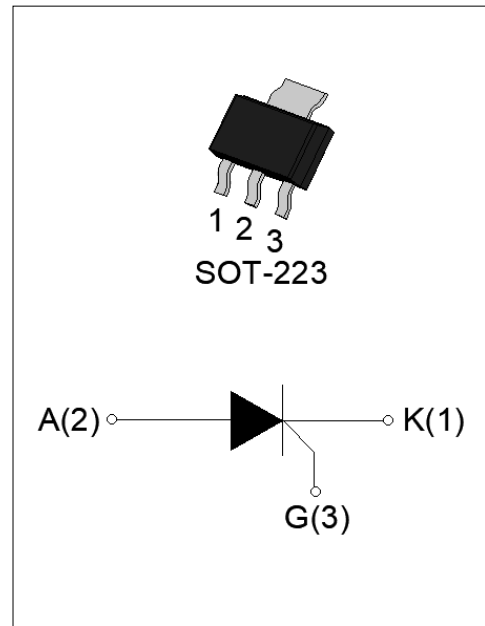
Rev.A.1.1

DESCRIPTION

The JX020V SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package SOT-223 is RoHS compliant.

PARAMETERS

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	≤ 200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
Average on-state current ($T_c=72^\circ C$)	$I_{T(AV)}$	1.3	A
RMS on-state current ($T_c=72^\circ C$)	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	20	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		22	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	2	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^\circ C$)	I_{GM}	1.2	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.2	W

Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{pp}	0.5	kV

NOTE 1: Operating junction temperature T_j is up to 125°C when a resistor $\leq 1\text{k}\Omega$ is connected between Gate and Cathode. Without this resistor, the T_j is up to 110°C only.

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.05\text{A}$	-	-	5	mA
dV/dt	$V_D=400\text{V}$ $T_j=125^\circ\text{C}$ $R_{GK}=1\text{k}\Omega$	20	-	-	V/ μs

JX020V

 **JieJie Microelectronics Co., Ltd.**

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FIG.1: Maximum power dissipation versus RMS on-state current

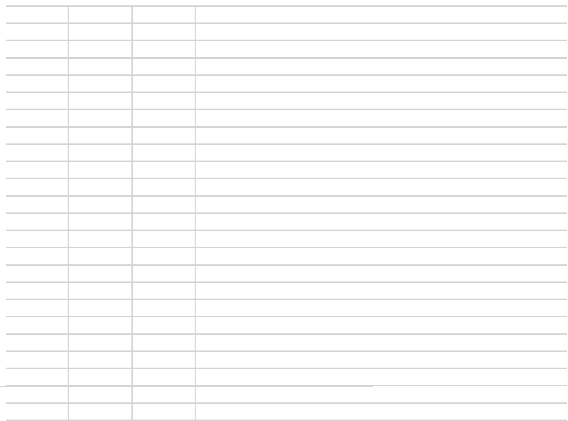


FIG.2: RMS on-state current versus case temperature'x#d2 f 0 bx -5 Q'wg3...#'"Wag8 v9Cb



FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

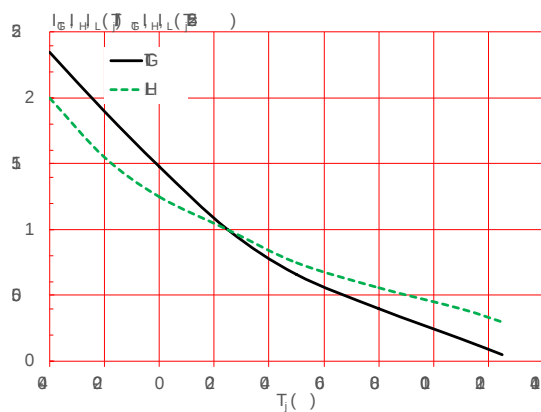
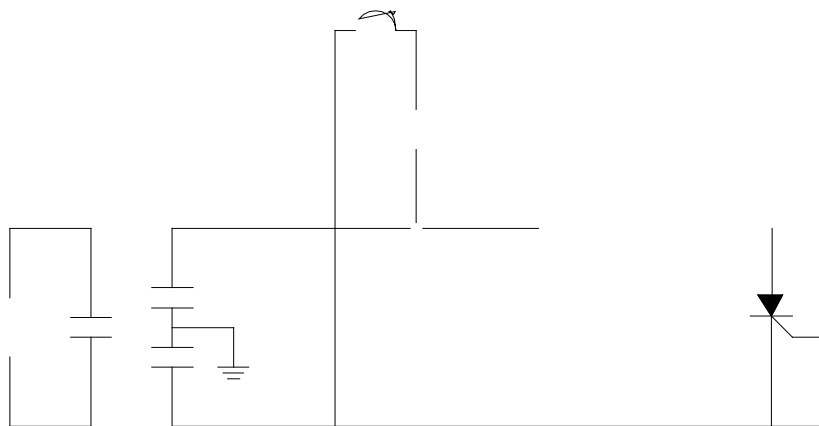


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



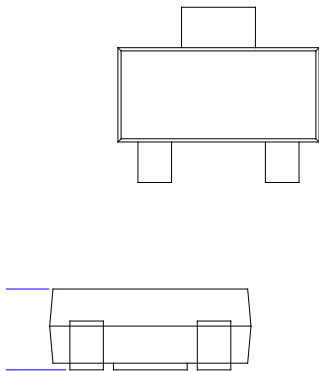
BERN I A170

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(μA)	Package	Base qty. (pcs)	Delivery mode
JX020V	600	≤ 200	SOT-223	4,000	Tape & Reel

Document Revision History

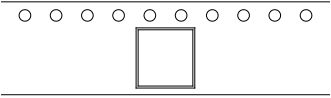
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update
Oct.23, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKGE MECHANICAL



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.50	1.60	1.80	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.90	3.00	3.10	0.114	0.118	0.122
B1	0.60	0.70	0.80	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
E	3.30	3.50	3.70	0.130	0.138	0.146
F	4.40			0.173		
F1	2.20			0.087		
G	0.50		1.00	0.020		0.039
H	1.50	1.75	2.00	0.059	0.069	0.079
J	6.70	7.00	7.30	0.264	0.276	0.287
K						

DELETED



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

